ABSTRACT

ACCUMULATION MODE MULTIPLE GATE TRANSISTOR

A transistor (1) having, a fin (2) and a gate electrode (3) extending on more than one side of the fin (2) to comprise more than one gate (9) of the transistor (1), and a dopant in each of a source (6), drain (7) and a channel region (8), comprising a single dopant type.

(FIG. 1)